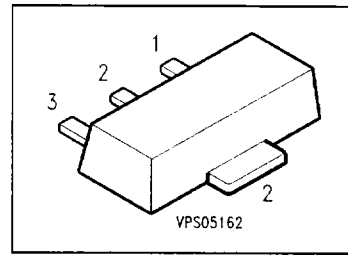
SIEMENS

PNP Silicon Darlington Transistors

BCV 28
BCV 48

- For general AF applications
- High collector current
- High current gain
- Complementary types: BCV 29, BCV 49 (NPN)



Type	Marking	Ordering Code (tape and reel)	Pin Configuration 1	2	3	4	Package[1]
BCV 28	ED	Q62702-C1852	B	C	E	C	SOT-89
BCV 48	EE	Q62702-C1854					

Maximum Ratings

Parameter	Symbol	Values BCV 28	BCV 48	Unit
Collector-emitter voltage	V_{CE0}	30	60	V
Collector-base voltage	V_{CB0}	40	80	
Emitter-base voltage	V_{EB0}	10	10	
Collector current	I_C	500		mA
Peak collector current	I_{CM}	800		
Base current	I_B	100		
Peak base current	I_{BM}	200		
Total power dissipation, T_S = 124 °C	P_{tot}	1		W
Junction temperature	T_j	150		°C
Storage temperature range	T_{stg}	– 65 ... + 150		

Thermal Resistance

Junction - ambient[2]	$R_{th\,JA}$	≤ 72	K/W
Junction - soldering point	$R_{th\,JS}$	≤ 17	

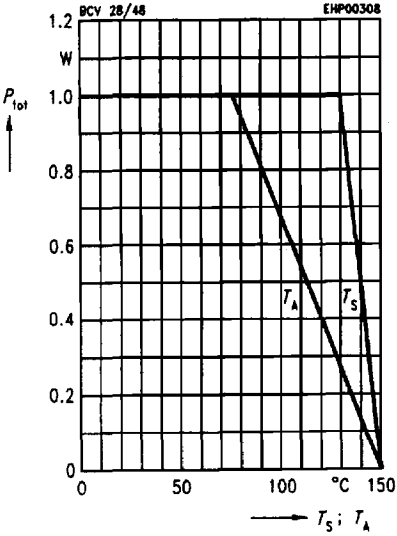
[1] For detailed information see chapter Package Outlines.
[2] Package mounted on epoxy pcb 40 mm × 40 mm × 1.5 mm/6 cm² Cu.

Electrical Characteristics
at T_A = 25 °C, unless otherwise specified.

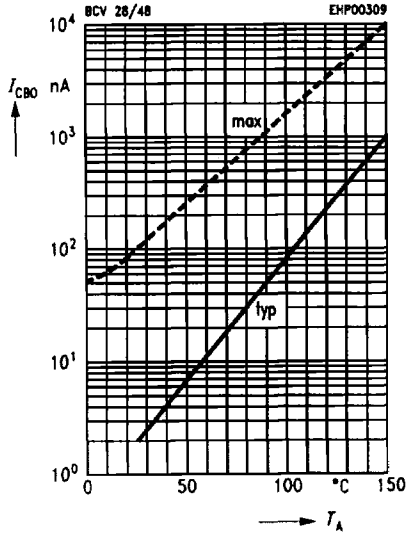
Parameter		Symbol	Values			Unit
			min.	typ.	max.	
DC characteristics						
Collector-emitter breakdown voltage I_C = 10 mA		$V_{(BR)CEO}$				V
	BCV 28		30	–	–	
	BCV 48		60	–	–	
Collector-base breakdown voltage I_C = 100 µA		$V_{(BR)CBO}$				
	BCV 28		40	–	–	
	BCV 48		80	–	–	
Emitter-base breakdown voltage, I_E = 10 µA		$V_{(BR)EBO}$	10	–	–	
Collector cutoff current		I_{CBO}				
V_{CB} = 30 V	BCV 28		–	–	100	nA
V_{CB} = 60 V	BCV 48		–	–	100	nA
V_{CB} = 30 V, T_A = 150 °C	BCV 28		–	–	10	µA
V_{CB} = 60 V, T_A = 150 °C	BCV 48		–	–	10	µA
Emitter cutoff current, V_{EB} = 4 V		I_{EBO}	–	–	100	nA
DC current gain[1]		h_{FE}				–
I_C = 100 µA, V_{CE} = 1 V	BCV 28		4000	–	–	
	BCV 48		2000	–	–	
I_C = 10 mA, V_{CE} = 5 V	BCV 28		10000	–	–	
	BCV 48		4000	–	–	
I_C = 100 mA, V_{CE} = 5 V	BCV 28		20000	–	–	
	BCV 48		10000	–	–	
I_C = 0.5 A, V_{CE} = 5 V	BCV 28		4000	–	–	
	BCV 48		2000	–	–	
Collector-emitter saturation voltage[1] I_C = 100 mA, I_B = 0.1 mA		V_{CEsat}	–	–	1	V
Base-emitter saturation voltage[1] I_C = 100 mA; I_B = 0.1 mA		V_{BEsat}	–	–	1.5	
AC characteristics						
Transition frequency I_C = 50 mA, V_{CE} = 5 V, f = 20 MHz		f_t	–	200	–	MHz
Output capacitance V_{CB} = 10 V, f = 1 MHz		C_{obo}	–	4.5	–	pF

[1] Pulse test: $t \leq 300$ µs, D = 2 %.

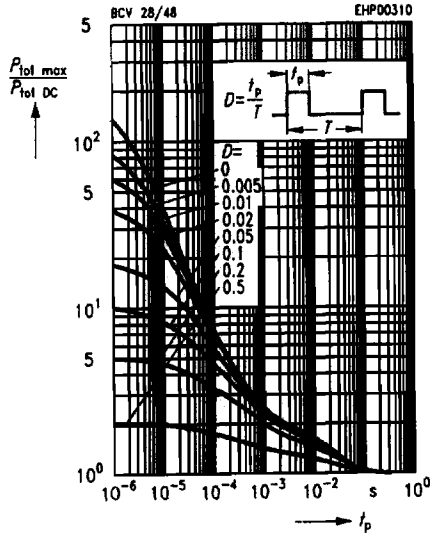
Total power dissipation $P_{tot} = f(T_A^*; T_S)$
* Package mounted on epoxy



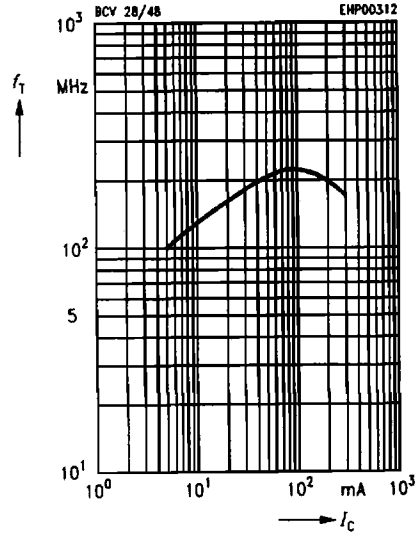
Collector cutoff current $I_{CBO} = f(T_A)$
$V_{CB} = V_{CE\,max}$



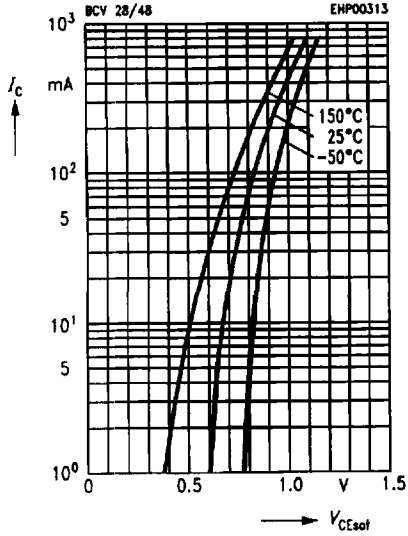
Permissible pulse load $P_{tot\,max}/P_{tot\,DC} = f(t_p)$



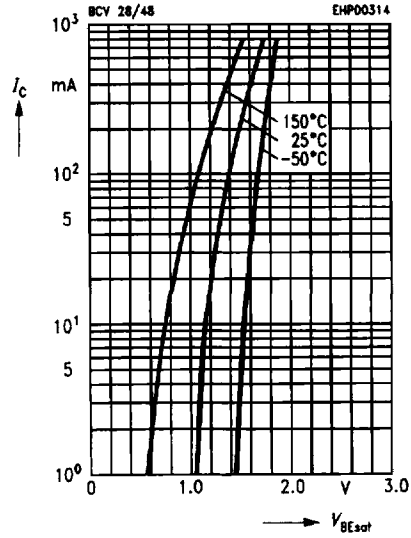
Transition frequency $f_T = f(I_C)$
$V_{CE} = 5$ V



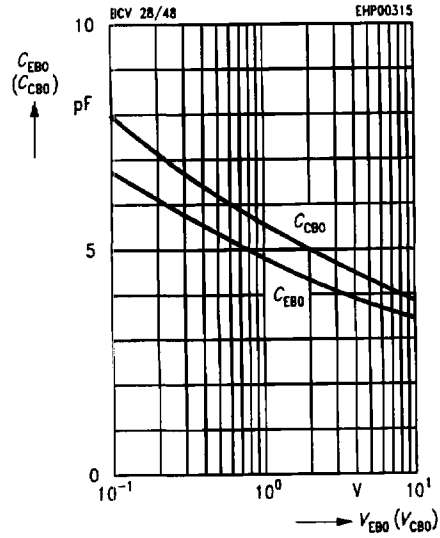
Collector-emitter saturation voltage
$I_C = f(V_{CEsat})$
$h_{FE} = 1000$



Base-emitter saturation voltage
$I_C = f(V_{BEsat})$
$h_{FE} = 1000$



Collector-base capacitance $C_{CBO} = f(V_{CBO})$
Emitter-base capacitance $C_{EBO} = f(V_{EBO})$



DC current gain $h_{FE} = f(I_C)$
$V_{CE} = 5$ V